STD3LN80K5

N-channel 800 V, 2.75 Ω typ., 2 A MDmesh™ K5 Power MOSFET in a DPAK package

Datasheet - production data

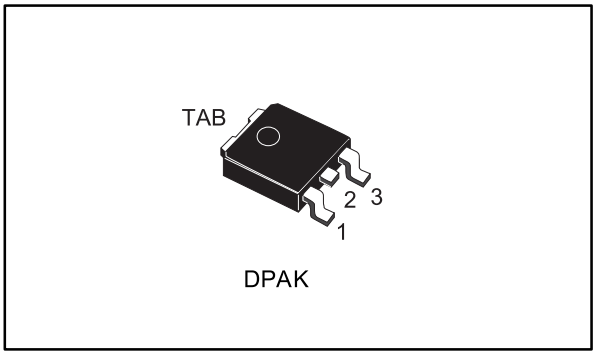
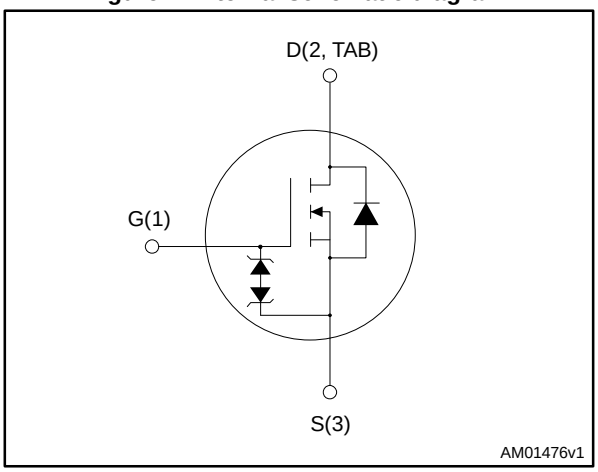


Figure 1: Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max	I_D
STD3LN80K5	800 V	3.25 Ω	2 A

- Industry's lowest $R_{DS(on)}$ x area
- Industry's best FoM (figure of merit)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This very high voltage N-channel Power MOSFET is designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1: Device summary

Order code	Marking	Package	Packing
STD3LN80K5	3LN80K5	DPAK	Tape and reel

This is information on a product in full production.

Contents

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at T_C = 25 °C	2	A
I_D	Drain current (continuous) at T_C = 100 °C	1.25	A
I_D (1)	Drain current (pulsed)	8	A
P_{TOT}	Total dissipation at T_C = 25 °C	45	W
dv/dt (2)	Peak diode recovery voltage slope	4.5	V/ns
dv/dt (3)	MOSFET dv/dt ruggedness	50	
T_{stg}	Storage temperature range	- 55 to 150	°C
T_j	Operating junction temperature range		

Notes:

(1)Pulse width limited by safe operating area.

(2)I_{SD} ≤ 2 A, di/dt ≤ 100 A/µs; V_{DSpeak} < $V_{(BR)DSS}$, V_{DD} = 640 V

(3)V_{DS} ≤ 640 V.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	2.78	°C/W
$R_{thj\text{-}pcb}$ (1)	Thermal resistance junction-pcb	50	°C/W

Notes:

(1)When mounted on 1inch² FR-4 board, 2 oz Cu.

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	0.7	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25°C, I_D = I_{AR}; V_{DD} = 50 V)	155	mJ

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 5: On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0 V	800			V
I_{DSS}	Zero gate voltage drain current	V_{DS} = 800 V, V_{GS} = 0 V			1	µA
		V_{DS} = 800 V, V_{GS} = 0 V, T_C = 125 °C(1)			50	µA
I_{GSS}	Gate body leakage current	V_{GS} = ± 20 V, V_{GS} = 0 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 100 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 1 A		2.75	3.25	Ω

Notes:

(1)Defined by design, not subject to production test.

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	102	-	pF
C_{oss}	Output capacitance		-	11	-	pF
C_{rss}	Reverse transfer capacitance		-	0.1	-	pF
C_{otr}(1)	Equivalent capacitance time related	V_{DS} = 0 to 640 V, V_{GS} = 0 V	-	20	-	pF
C_{oer}(2)	Equivalent capacitance energy related		-	7	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, I_D = 0 A	-	12	-	Ω
Q_g	Total gate charge	V_{DD} = 640 V, I_D = 2 A, V_{GS} = 10 V (see *Figure 15: "Test circuit for gate charge behavior"*)	-	2.63	-	nC
Q_{gs}	Gate-source charge		-	0.91	-	nC
Q_{gd}	Gate-drain charge		-	1.53	-	nC

Notes:

(1)Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

(2)Energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 400 V, I_D = 1 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 14: "Test circuit for resistive load switching times"* and *Figure 19: "Switching time waveform"*)	-	6.2	-	ns
t_r	Rise time		-	7	-	ns
$t_{d(off)}$	Turn-off delay time		-	30	-	ns
t_f	Fall time		-	26	-	ns

Table 8: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		2	A
I_{SDM}(1)	Source-drain current (pulsed)		-		8	A
V_{SD}(2)	Forward on voltage	I_{SD} = 2 A, V_{GS} = 0 V	-		1.5	V
t_{rr}	Reverse recovery time	I_{SD} = 2 A, di/dt = 100 A/µs, V_{DD} = 60 V (see *Figure 16: "Test circuit for inductive load switching and diode recovery times"*)	-	210		ns
Q_{rr}	Reverse recovery charge		-	0.8		µC
I_{RRM}	Reverse recovery current		-	7.6		A
t_{rr}	Reverse recovery time	I_{SD} = 2 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_j = 150 °C, (see *Figure 16: "Test circuit for inductive load switching and diode recovery times"*)	-	345		ns
Q_{rr}	Reverse recovery charge		-	1.2		µC
I_{RRM}	Reverse recovery current		-	7.2		A

Notes:

(1)Pulse width limited by safe operating area.

(2)Pulsed: pulse duration = 300 µs, duty cycle 1.5%.

Table 9: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	I_{GS} = ± 1 mA, I_D = 0 A	30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

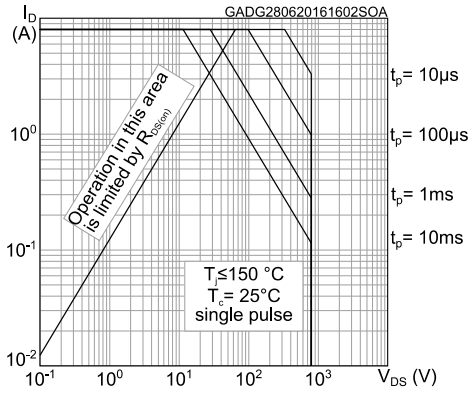


Figure 3: Thermal impedance

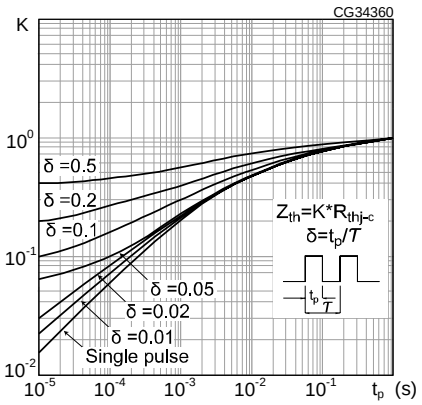


Figure 4: Output characteristics

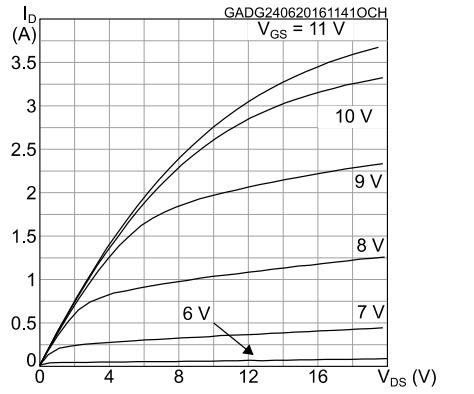


Figure 5: Transfer characteristics

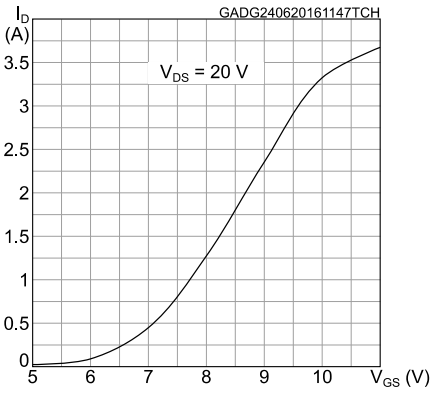


Figure 6: Gate charge vs gate-source voltage

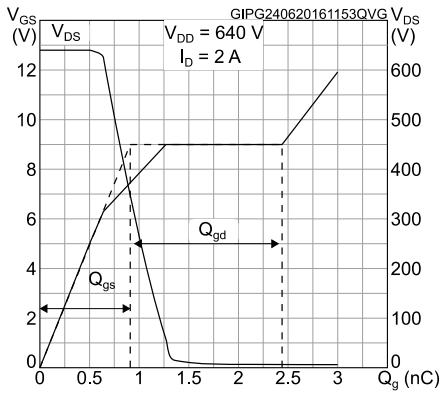


Figure 7: Static drain-source on-resistance

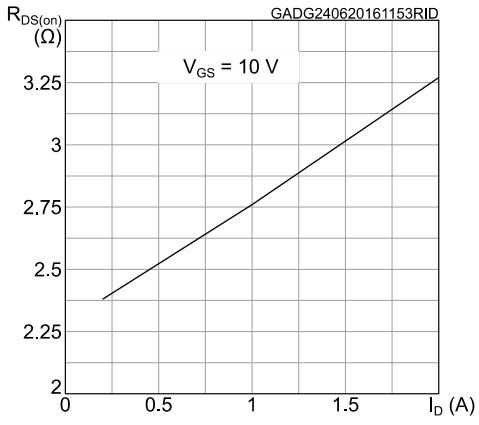


Figure 8: Capacitance variations

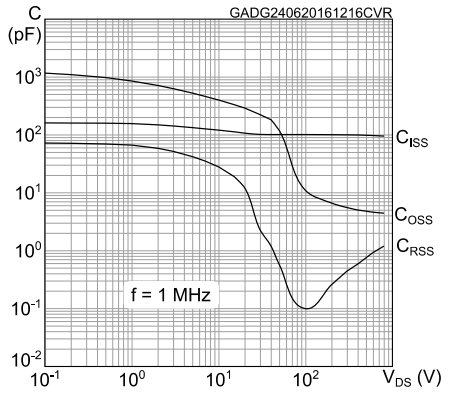


Figure 9: Source-drain diode forward characteristics

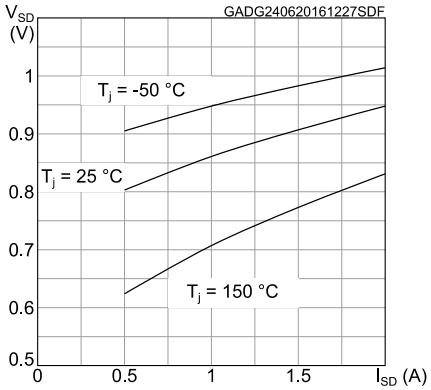


Figure 10: Normalized gate threshold voltage vs temperature

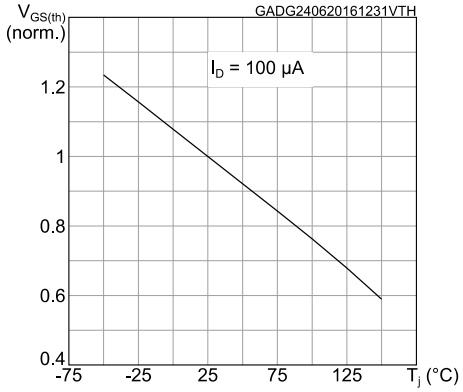


Figure 11: Normalized on-resistance vs temperature

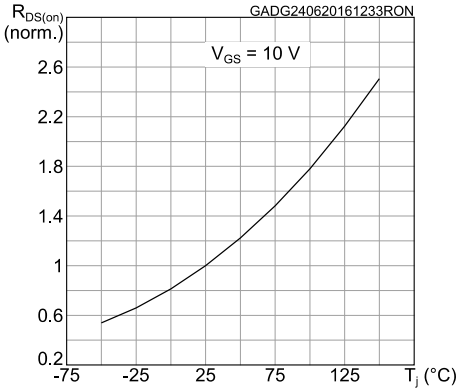


Figure 12: Normalized V(BR)DSS vs temperature

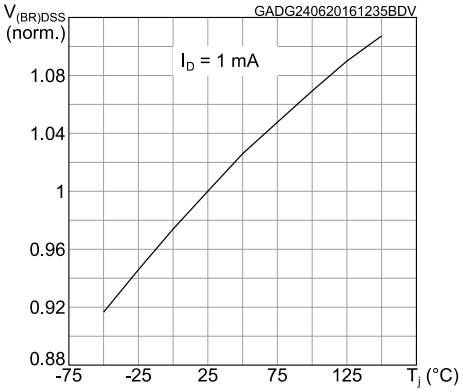
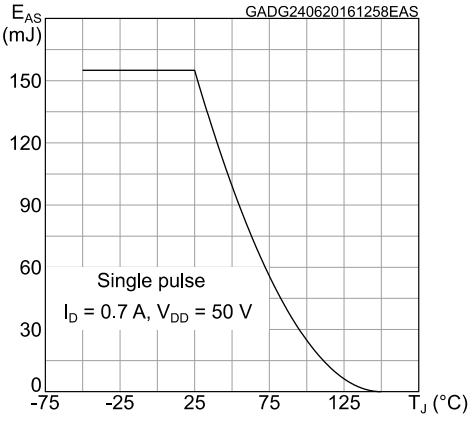


Figure 13: Maximum avalanche energy vs starting TJ



3 Test circuits

Figure 14: Test circuit for resistive load switching times

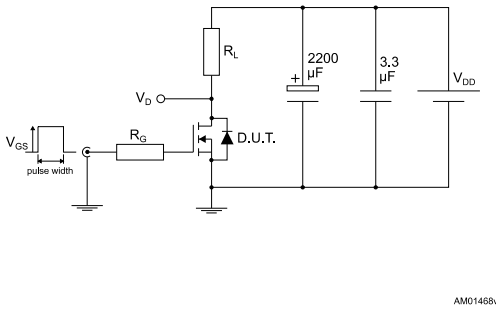


Figure 15: Test circuit for gate charge behavior

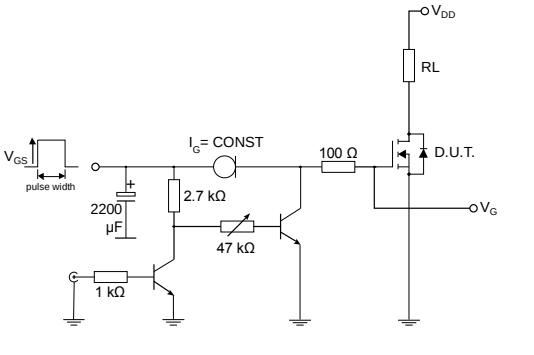


Figure 16: Test circuit for inductive load switching and diode recovery times

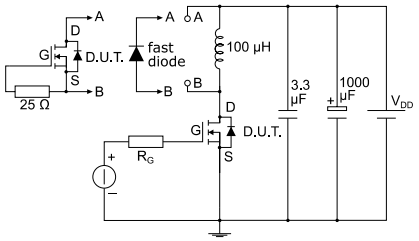


Figure 17: Unclamped inductive load test circuit

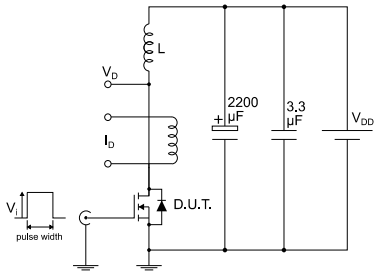


Figure 18: Unclamped inductive waveform

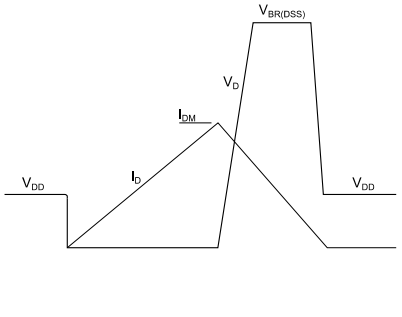
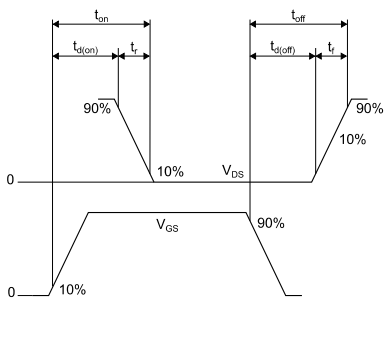


Figure 19: Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

4.1 DPAK package information

Figure 20: DPAK (TO-252) type A package outline

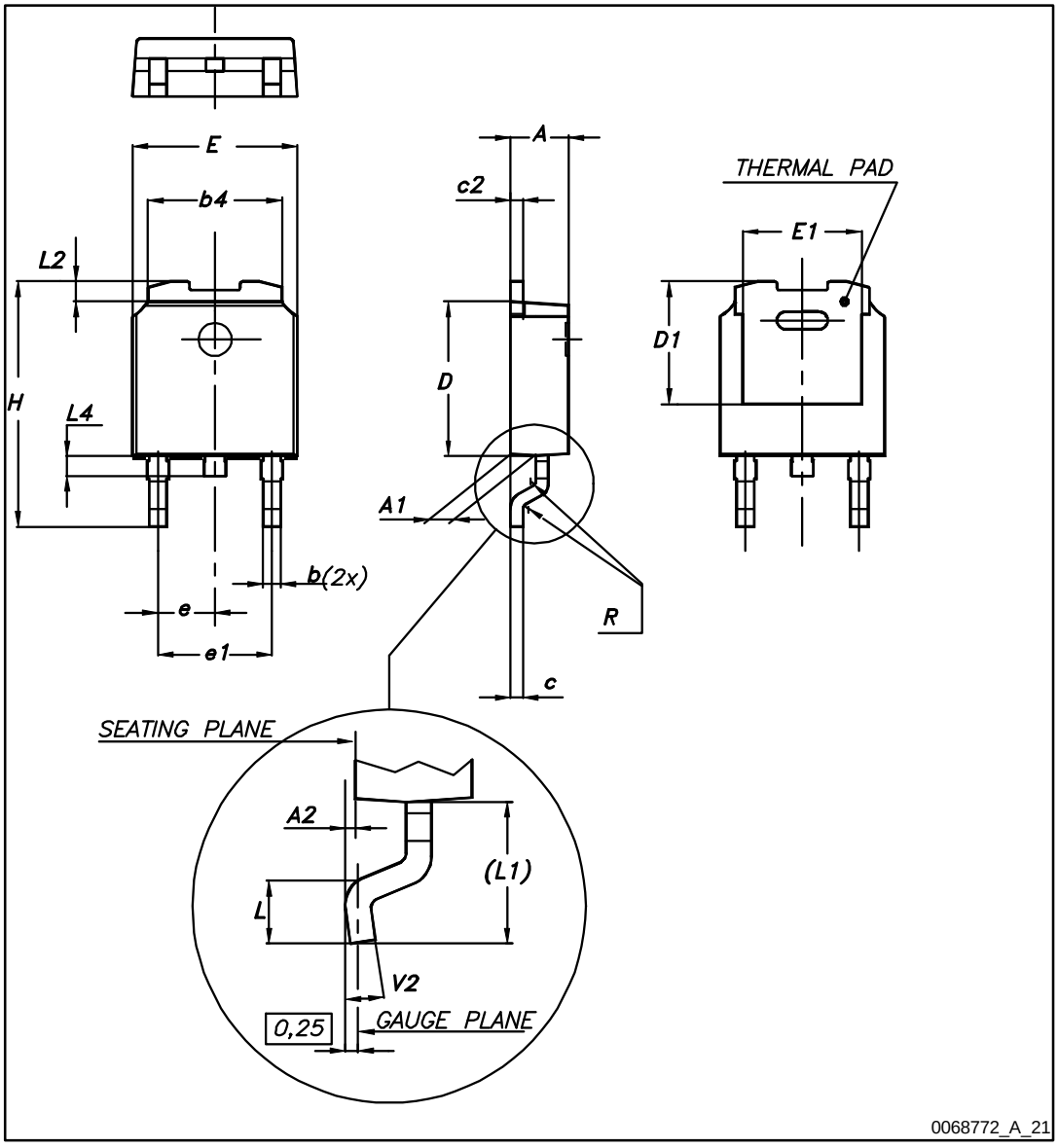
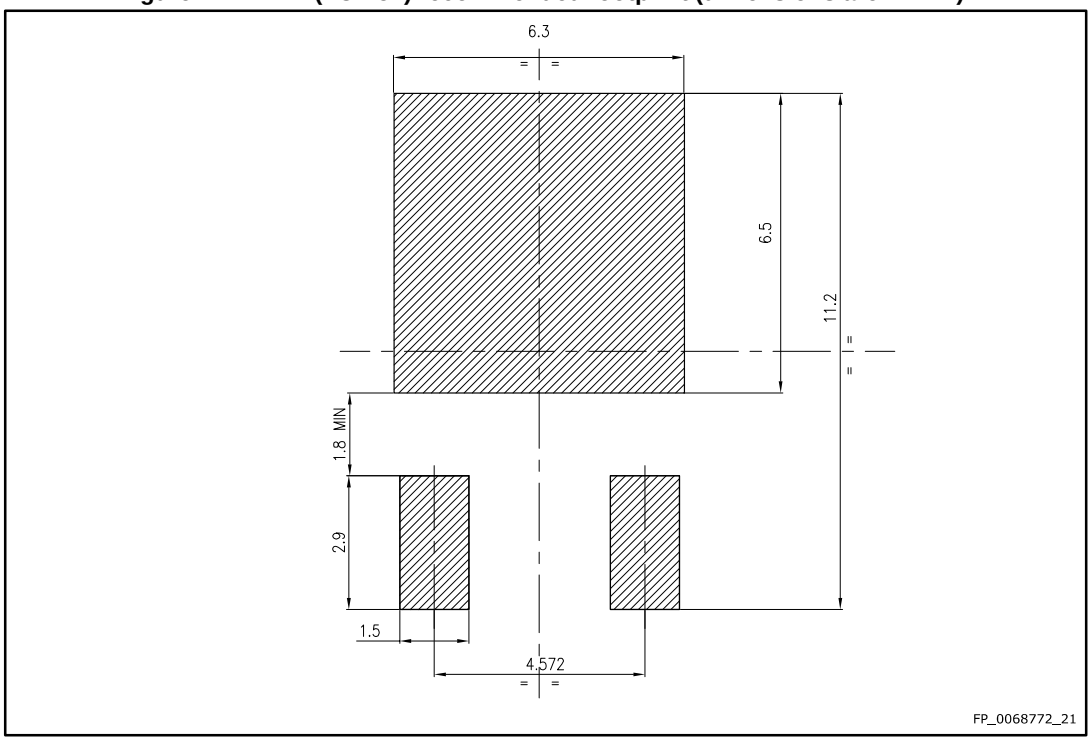


Table 10: DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 21: DPAK (TO-252) recommended footprint (dimensions are in mm)



4.2 DPAK packing information

Figure 22: DPAK (TO-252) tape outline

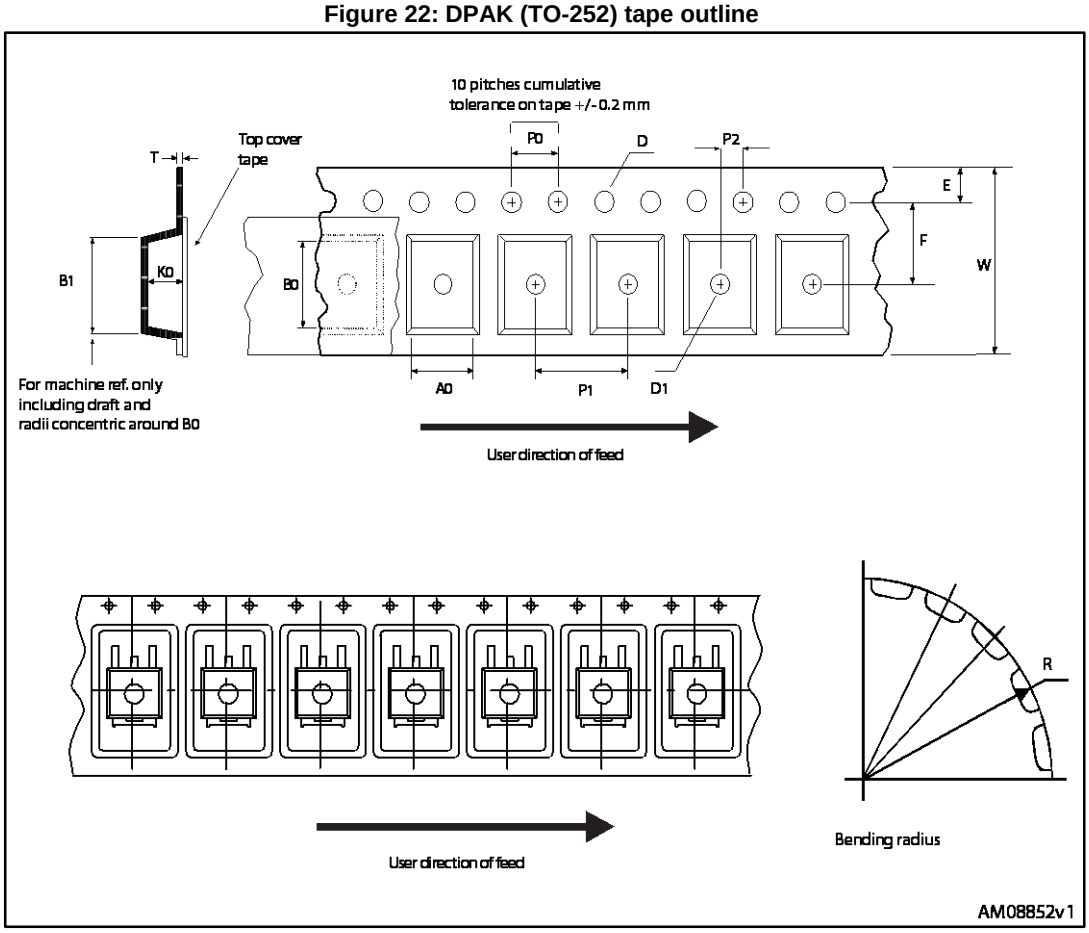


Figure 23: DPAK (TO-252) reel outline

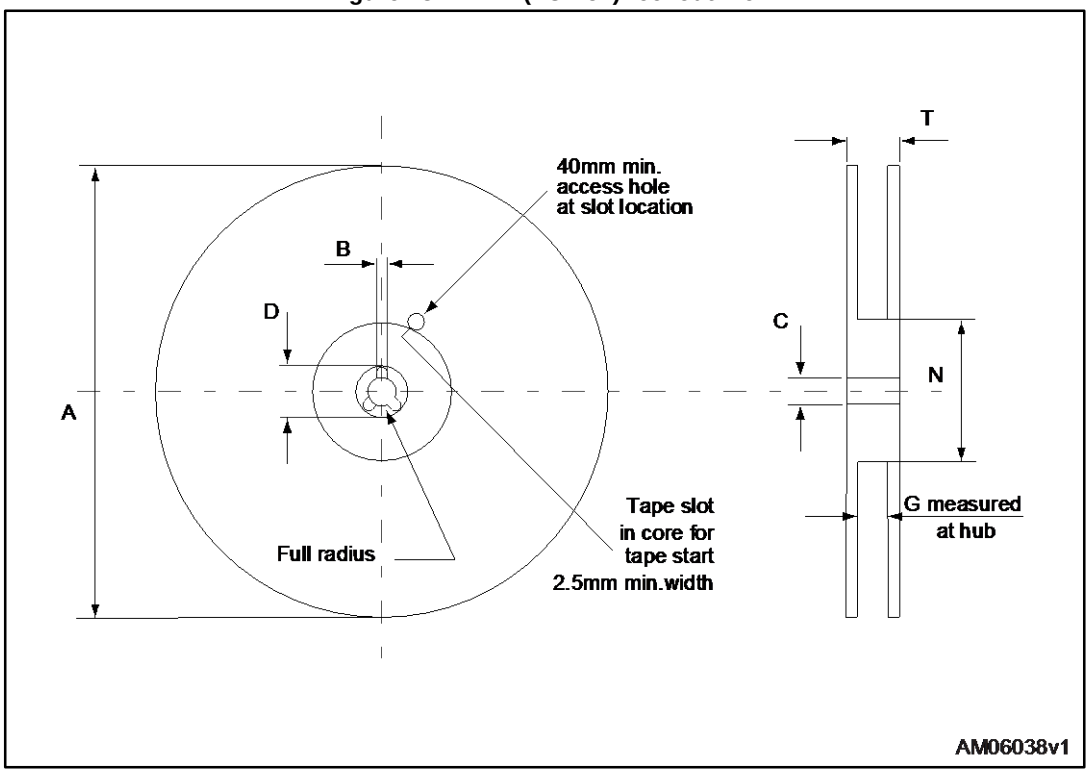


Table 11: DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

5 Revision history

Table 12: Document revision history

Date	Revision	Changes
13-May-2015	1	Initial release
27-Jul-2016	2	Updated title and features in cover page. Updated *Section 1: "Electrical ratings"* and *Section 2: "Electrical characteristics"*. Added *Section 2.1: "Electrical characteristics (curves)"*. Document status promoted from preliminary to production data. Minor text changes.

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